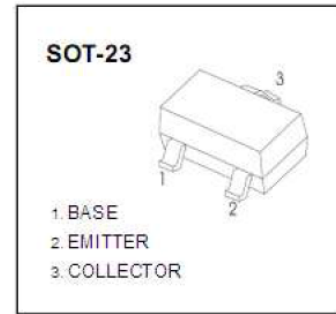


S8550 (PNP)

印章/Marking: 2TY

用途/Applications:

用于功率放大电路, 与 S8050 互补。



极限参数/Absolute maximum ratings (Ta=25°C)

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
集电极-基极电压/Collector-Base Voltage	V_{CB0}	-40	V
集电极-发射极电压/Collector-Emitter Voltage	V_{CE0}	-25	V
发射极-基极电压/Emitter-Base Voltage	V_{EB0}	-5	V
集电极连续电流/Collector Current Continuous	I_C	-0.5	A
集电极耗散功率/Collector Power Dissipation	P_C	0.3	W
结温/Junction Temperature	T_j	150	°C
储存温度/Storage Temperature	T_{stg}	-55~150	°C

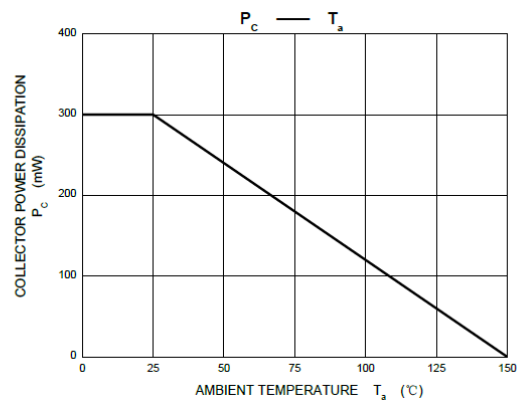
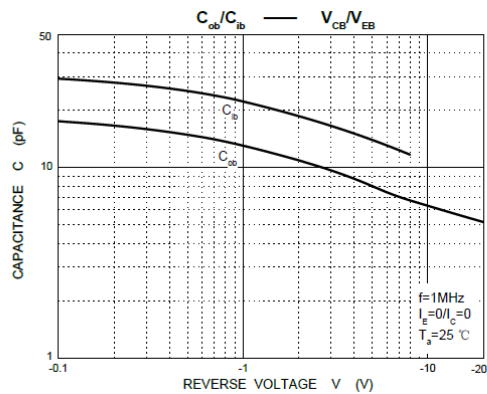
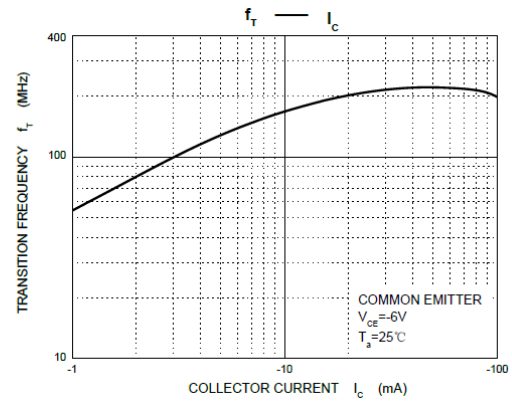
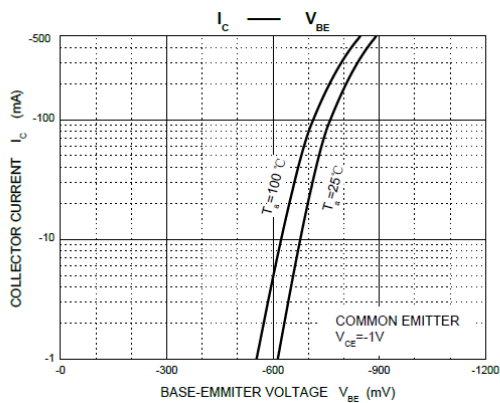
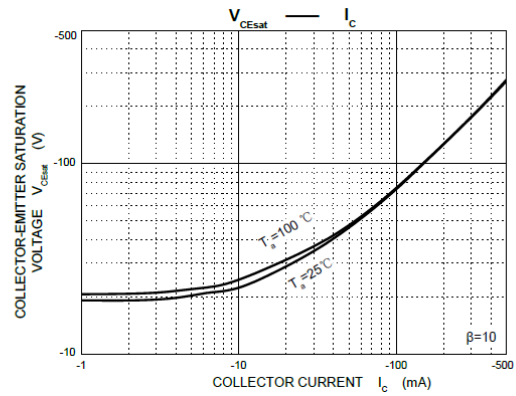
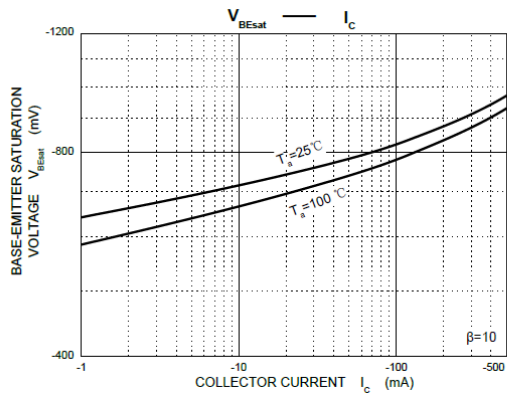
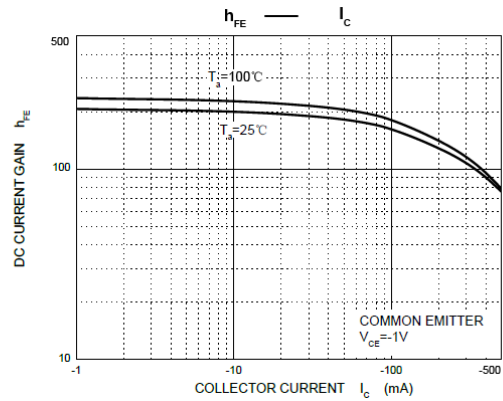
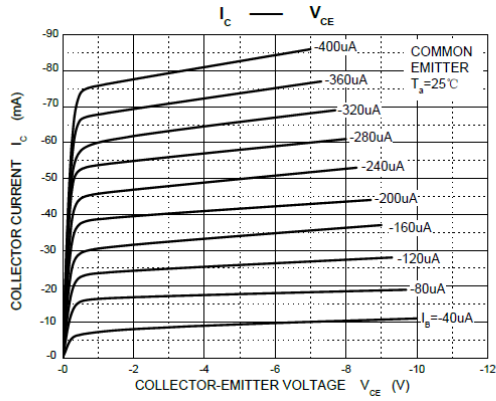
电性能参数/Electrical characteristics (Ta=25°C)

参数	符号	测试条件	最小值	典型值	最大值	单位
集电极-基极击穿电压	$V_{BR(CB0)}$	$I_C = -100 \mu A, I_E = 0$	-40			V
集电极-发射极击穿电压	$V_{BR(CE0)}$	$I_C = -1mA, I_B = 0$	-25			V
发射极-基极击穿电压	$V_{BR(EB0)}$	$I_E = -100 \mu A, I_C = 0$	-5			V
集电极截止电流	I_{CB0}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
发射极截止电流	I_{EB0}	$V_{EB} = -3V, I_C = 0$			-0.1	μA
集电极发射极穿透电流	I_{CE0}	$V_{CE} = -20V, I_B = 0$			-0.1	μA
直流电流增益	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -50mA$	120		400	
直流电流增益	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	50			
集电极-发射极饱和压降	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-0.6	V
基极-发射极饱和压降	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.2	V
特征频率	f_T	$V_{CE} = -6V, I_C = -20mA, f = 30MHz$	150			MHz

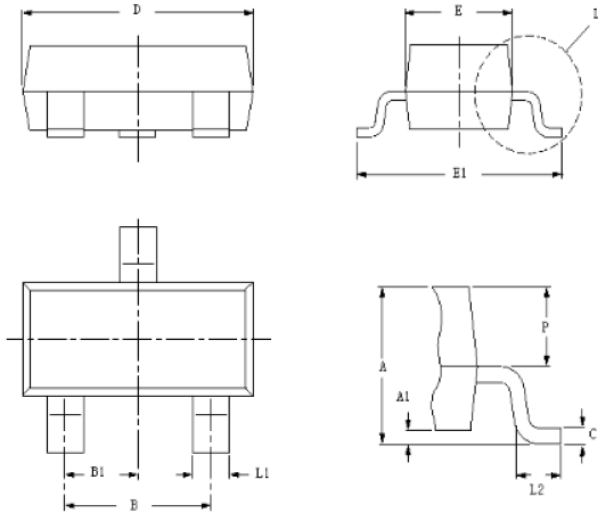
h_{FE} 分档/Classification of $h_{FE(1)}$

档位/Rank	L	H
范围/Range	120~200	200~350

Typical Characteristics



SOT-23 Package Outline Dimensions



Symbol	Dim in mm	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
L1	0.350	0.500
C	0.090	0.150
D	2.800	3.000
E	1.250	1.350
E1	2.250	2.550
B	1.800	2.000
B1	0.950 TYP	
L2	0.200	0.450
P	0.550	0.600

Mold Surface roughness: < 4um

SOT-23 Tape and Reel

PKG TYPE	W	P	E	F	D	D1	Po	Po10	P2	A0	B0	K0	T
SOT-23	8.00	4.00	1.75	3.50	1.50	1.00	4.00	40.00	2.00	3.15	2.77	1.22	0.20
Tolerance	+0.3/-0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.2	±0.05	±0.1	±0.1	±0.1	±0.02

